

FDM606P

P-Channel 1.8V Logic Level Power Trench® MOSFET

General Description

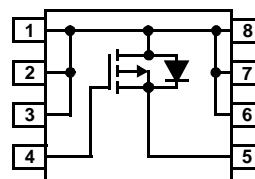
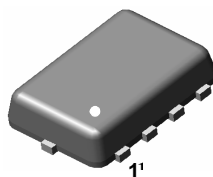
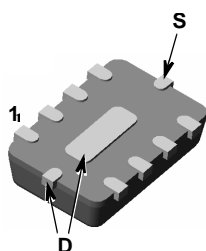
This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance. These devices are well suited for portable electronics applications.

Features

- Fast switching
- $r_{DS(ON)} = 0.026\Omega$ (Typ), $V_{GS} = -4.5V$
- $r_{DS(ON)} = 0.033\Omega$ (Typ), $V_{GS} = -2.5V$
- $r_{DS(ON)} = 0.052\Omega$ (Typ), $V_{GS} = -1.8V$

Applications

- Load switch
- Battery charge
- Battery disconnect circuits



MicroFET 3x2-8

MOSFET Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	± 8	V
I_D	Drain Current		
	Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = -4.5V$)	-6.8	A
	Continuous ($T_C = 100^\circ\text{C}$, $V_{GS} = -2.5V$)	-3.8	A
	Continuous ($T_C = 100^\circ\text{C}$, $V_{GS} = -1.8V$)	-3.0	A
	Pulsed	Figure 4	
P_D	Power dissipation	1.92	W
	Derate above 25°C	15.4	mW/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case (Note 1)	6.0	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (Note 2)	65	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (Note 3)	208	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.06P	FDM606P	MicroFET3x2	178 mm	8 mm	3000

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

$B_{V_{DSS}}$	Drain to Source Breakdown Voltage	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{V}$ $V_{GS} = 0\text{V}$ $T_A = 100^\circ\text{C}$	-	-	-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(TH)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\mu\text{A}$	-0.4	-0.9	-1.5	V
$r_{DS(ON)}$	Drain to Source On Resistance	$I_D = -6.8\text{A}, V_{GS} = -4.5\text{V}$	-	0.026	0.030	Ω
		$I_D = -3.8\text{A}, V_{GS} = -2.5\text{V}$	-	0.033	0.038	
		$I_D = -3.0\text{A}, V_{GS} = -1.8\text{V}$	-	0.052	0.070	

Dynamic Characteristics

C_{ISS}	Input Capacitance	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$	-	2200	-	μF	
C_{OSS}	Output Capacitance		-	350	-	μF	
C_{RSS}	Reverse Transfer Capacitance		-	160	-	μF	
$Q_{g(TOT)}$	Total Gate Charge at -4.5V	$V_{GS} = 0\text{V}$ to -4.5V	$V_{DD} = -10\text{V}$ $I_D = -3.0\text{A}$ $I_g = 1.0\text{mA}$	-	20	30	nC
$Q_{g(-2.5)}$	Total Gate Charge at -2.5V	$V_{GS} = 0\text{V}$ to -2.5V		-	12	18	nC
Q_{gs}	Gate to Source Gate Charge			-	3.0	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	3.8	-	nC

Switching Characteristics ($V_{GS} = -4.5\text{V}$)

t_{ON}	Turn-On Time	$V_{DD} = -10\text{V}, I_D = -3.0\text{A}$ $V_{GS} = -4.5\text{V}, R_{GS} = 6.8\Omega$	-	-	81	ns
$t_{d(ON)}$	Turn-On Delay Time		-	9	-	ns
t_r	Rise Time		-	46	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	134	-	ns
t_f	Fall Time		-	71	-	ns
t_{OFF}	Turn-Off Time		-	-	308	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = -6.8\text{A}$	-	-0.9	-1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = -3.0\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	28	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = -3.0\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	20	nC

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the center drain pad. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by user's board design.
- $R_{\theta JA}$ is $65^\circ\text{C}/\text{W}$ (steady state) when mounted on a 1 inch² copper pad on FR-4.
- $R_{\theta JA}$ is $208^\circ\text{C}/\text{W}$ (steady state) when mounted on a minimum pad area.

Typical Characteristic $T_A = 25^\circ\text{C}$ unless otherwise noted

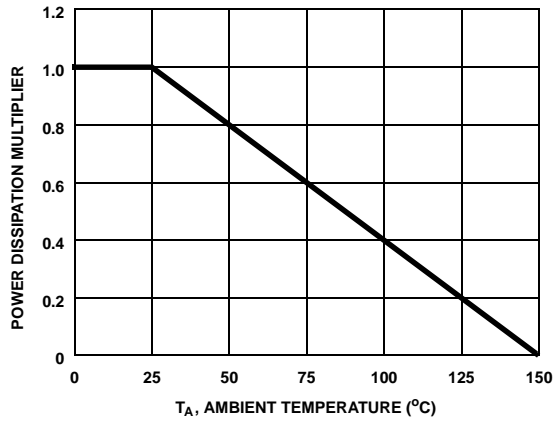


Figure 1. Normalized Power Dissipation vs Ambient Temperature

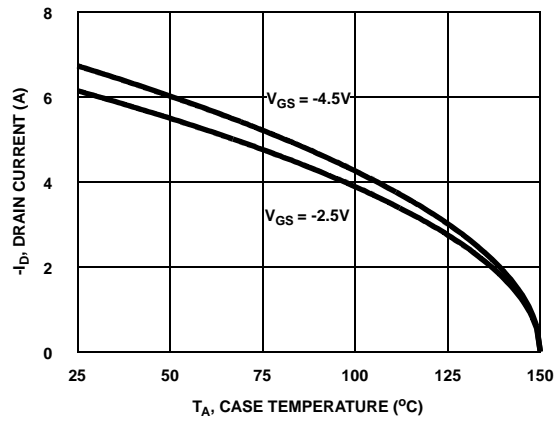


Figure 2. Maximum Continuous Drain Current vs Case Temperature

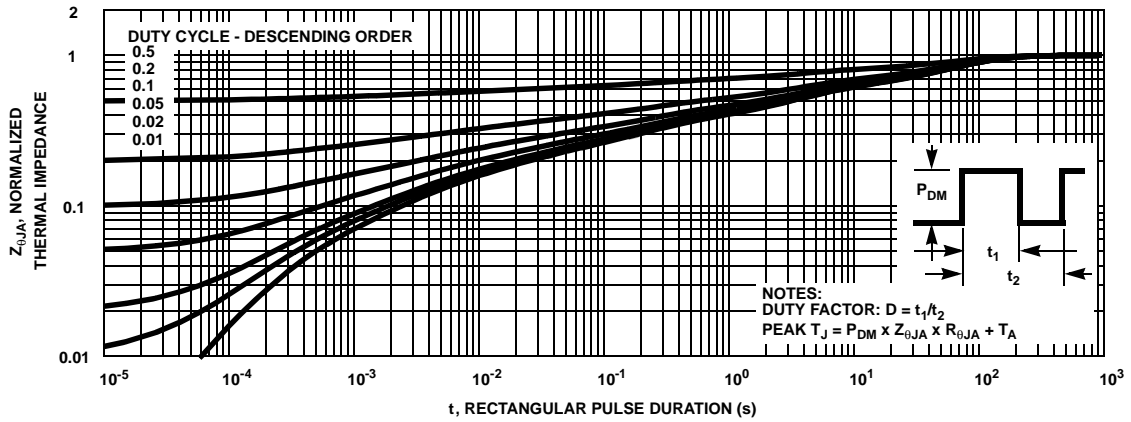


Figure 3. Normalized Maximum Transient Thermal Impedance

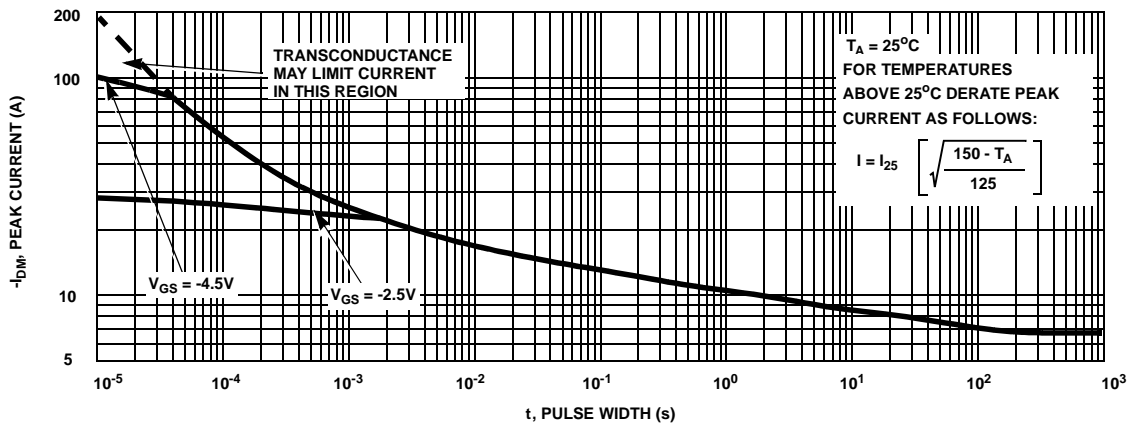


Figure 4. Peak Current Capability

Typical Characteristic (Continued) $T_A = 25^\circ\text{C}$ unless otherwise noted

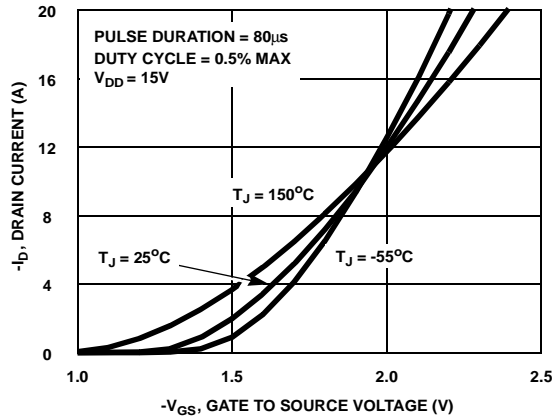


Figure 5. Transfer Characteristics

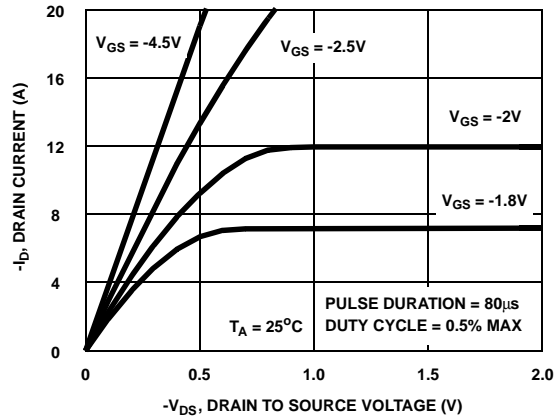


Figure 6. Saturation Characteristics

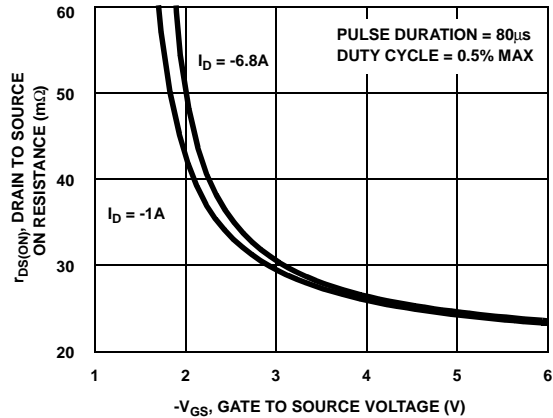


Figure 7. Drain to Source On Resistance vs Gate Voltage and Drain Current

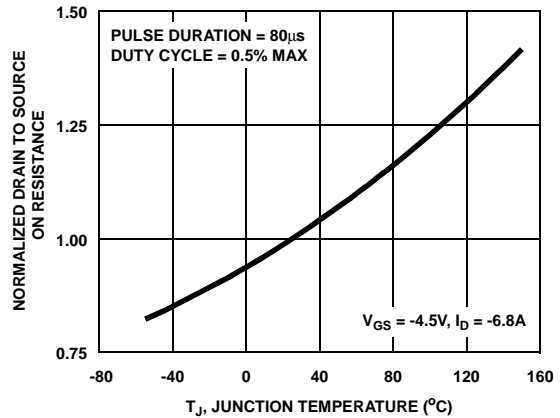


Figure 8. Normalized Drain to Source On Resistance vs Junction Temperature

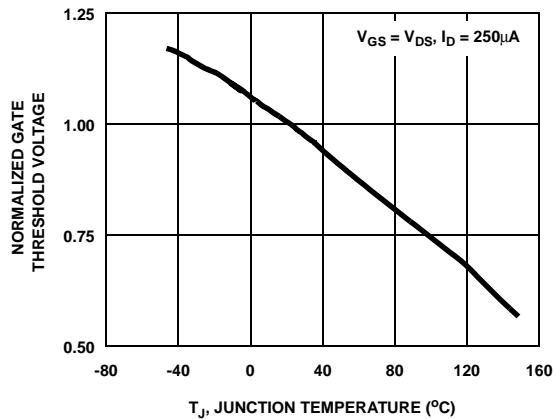


Figure 9. Normalized Gate Threshold Voltage vs Junction Temperature

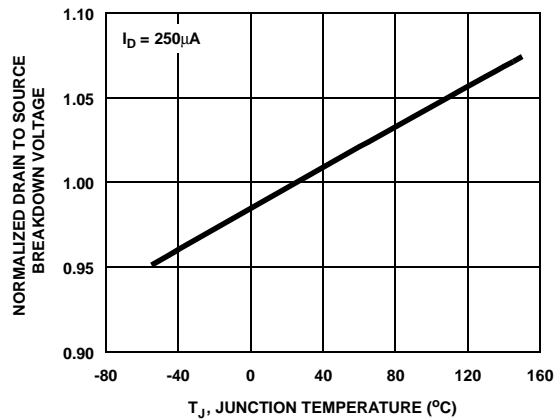


Figure 10. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

Typical Characteristic (Continued) $T_A = 25^\circ\text{C}$ unless otherwise noted

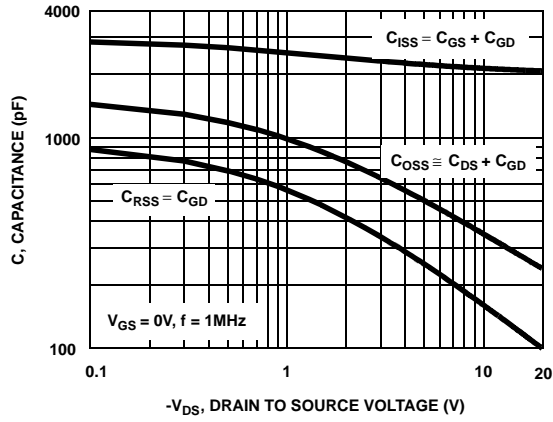


Figure 11. Capacitance vs Drain to Source Voltage

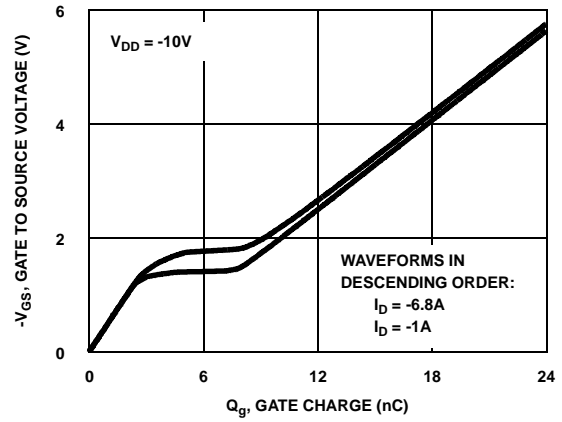


Figure 12. Gate Charge Waveforms for Constant Gate Currents

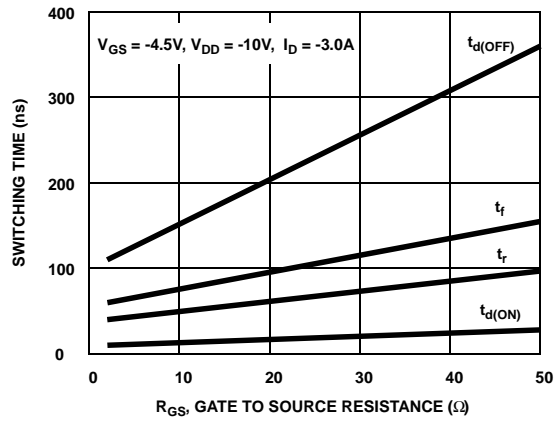


Figure 13. Switching Time vs Gate Resistance

Test Circuits and Waveforms

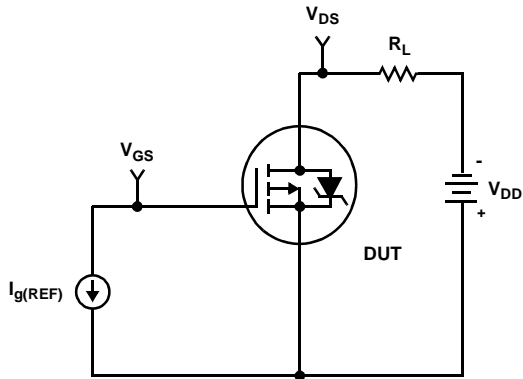


Figure 14. Gate charge Test Circuit

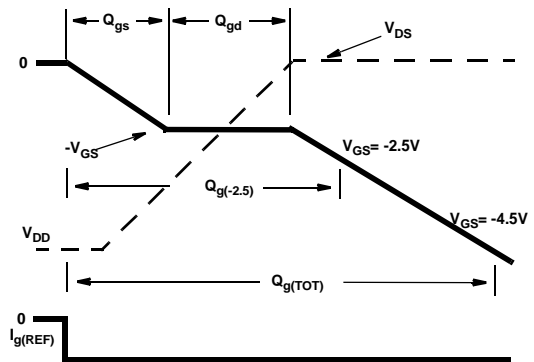


Figure 15. Gate Charge Waveforms

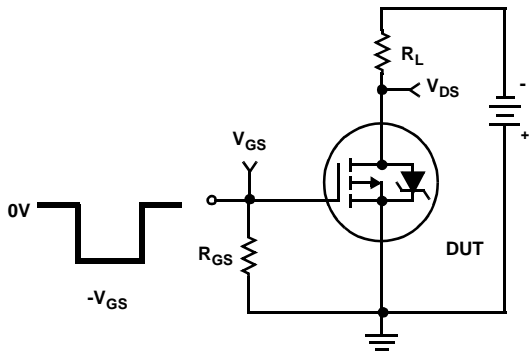


Figure 16. Switching Time Test Circuit

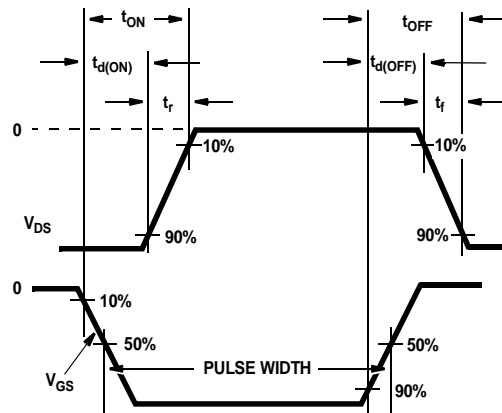


Figure 17. Switching Time Waveforms

Thermal Resistance vs. Mounting Pad Area

The maximum rated junction temperature, T_{JM} , and the thermal resistance of the heat dissipating path determines the maximum allowable device power dissipation, P_{DM} , in an application. Therefore the application's ambient temperature, T_A ($^{\circ}C$), and thermal resistance $R_{\theta JA}$ ($^{\circ}C/W$) must be reviewed to ensure that T_{JM} is never exceeded. Equation 1 mathematically represents the relationship and serves as the basis for establishing the rating of the part.

$$P_{DM} = \frac{(T_{JM} - T_A)}{Z_{\theta JA}} \quad (\text{EQ. 1})$$

In using surface mount devices such as the MicroFET package, the environment in which it is applied will have a significant influence on the part's current and maximum power dissipation ratings. Precise determination of P_{DM} is complex and influenced by many factors:

1. Mounting pad area onto which the device is attached and whether there is copper on one side or both sides of the board.
2. The number of copper layers and the thickness of the board.
3. The use of external heat sinks.
4. The use of thermal vias.
5. Air flow and board orientation.
6. For non steady state applications, the pulse width, the duty cycle and the transient thermal response of the part, the board and the environment they are in.

Fairchild provides thermal information to assist the designer's preliminary application evaluation. Figure 18 defines the $R_{\theta JA}$ for the device as a function of the top copper (component side) area. This is for a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power with no air flow. This graph provides the necessary information for calculation of the steady state junction temperature or power dissipation. Pulse applications can be evaluated using the Fairchild device Spice thermal model or manually utilizing the normalized maximum transient thermal impedance curve.

Thermal resistances corresponding to other copper areas can be obtained from Figure 18 or by calculation using Equation 2. The area, in square inches is the top copper area including the gate and source pads.

$$R_{\theta JA} = 58.9 + \frac{6.8}{(0.041 + Area)} \quad (\text{EQ. 2})$$

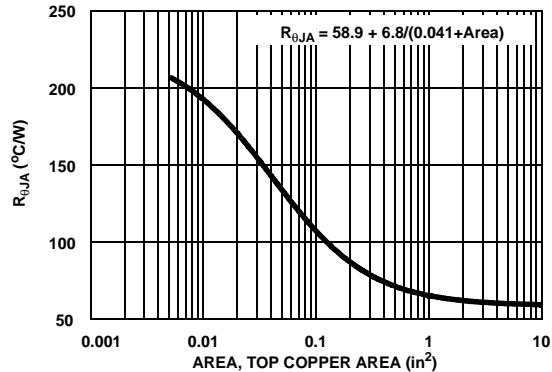


Figure 18. Thermal Resistance vs Mounting Pad Area

PSPICE Electrical Model

.SUBCKT FDM606P 2 1 3 ; rev Oct. 2001
 CA 12 8 18.3e-10
 CB 15 14 18.3e-10
 CIN 6 8 19.8e-10

DBODY 5 7 DBODYMOD
 DBREAK 7 11 DBREAKMOD
 DPLCAP 10 6 DPLCAPMOD

EBREAK 5 11 17 18 -23.4
 EDS 14 8 5 8 1
 EGS 13 8 6 8 1
 ESG 5 10 8 6 1
 EVTHRES 6 21 19 8 1
 EVTEMP 6 20 18 22 1

IT 8 17 1

LDRAIN 2 5 1e-9
 LGATE 1 9 1.1e-9
 LSOURCE 3 7 0.78e-9

MMED 16 6 8 8 MMEDMOD
 MSTRO 16 6 8 8 MSTROMOD
 MWEAK 16 21 8 8 MWEAKMOD

RBREAK 17 18 RBREAKMOD 1
 RDRAIN 50 16 RDRAINMOD 8.5e-3
 RGATE 9 20 16
 RLDRAIN 2 5 10
 RLGATE 1 9 11
 RLSOURCE 3 7 7.8
 RSLC1 5 51 RSLCMOD 1e-6
 RSLC2 5 50 1e3
 RSOURCE 8 7 RSOURCEMOD 11e-3
 RVTHRES 22 8 RVTHRESMOD 1
 RVTEMP 18 19 RVTEMPMOD 1

S1A 6 12 13 8 S1AMOD
 S1B 13 12 13 8 S1BMOD
 S2A 6 15 14 13 S2AMOD
 S2B 13 15 14 13 S2BMOD

VBAT 22 19 DC 1

ESLC 51 50 VALUE={(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)/(1e-6*97),2.5))}

.MODEL DBODYMOD D (IS = 8e-11 N=1.07 RS = 1.3e-2 TRS1 = 1e-3 TRS2 = 1e-6 XTI=0 IKF=0.2 CJO = 5.9e-10 TT = 14.5e-9 M = 0.47)

.MODEL DBREAKMOD D (RS = 5.3e-1 TRS1 = 5.5e-3 TRS2 = -9e-5)

.MODEL DPLCAPMOD D (CJO = 9.4e-10 IS = 1e-30 N = 10 M = 0.73)

.MODEL MMEDMOD PMOS (VTO = -0.96 KP = 1.3 IS=1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 16)

.MODEL MSTROMOD PMOS (VTO = -1.22 KP = 54 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)

.MODEL MWEAKMOD PMOS (VTO = -0.8 KP = 0.05 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 160 RS = 0.1)

.MODEL RBREAKMOD RES (TC1 = 7e-4 TC2 = -1e-7)

.MODEL RDRAINMOD RES (TC1 = 1.5e-3 TC2 = 4.9e-6)

.MODEL RSLCMOD RES (TC1 = 3.7e-3 TC2 = 7.8e-6)

.MODEL RSOURCEMOD RES (TC1 = 3e-3 TC2 = 5.2e-6)

.MODEL RVTHRESMOD RES (TC1 = 1.2e-3 TC2 = 1.2e-6)

.MODEL RVTEMPMOD RES (TC1 = -6.4e-4 TC2 = -1e-9)

.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 3.0 VOFF= 1.0)

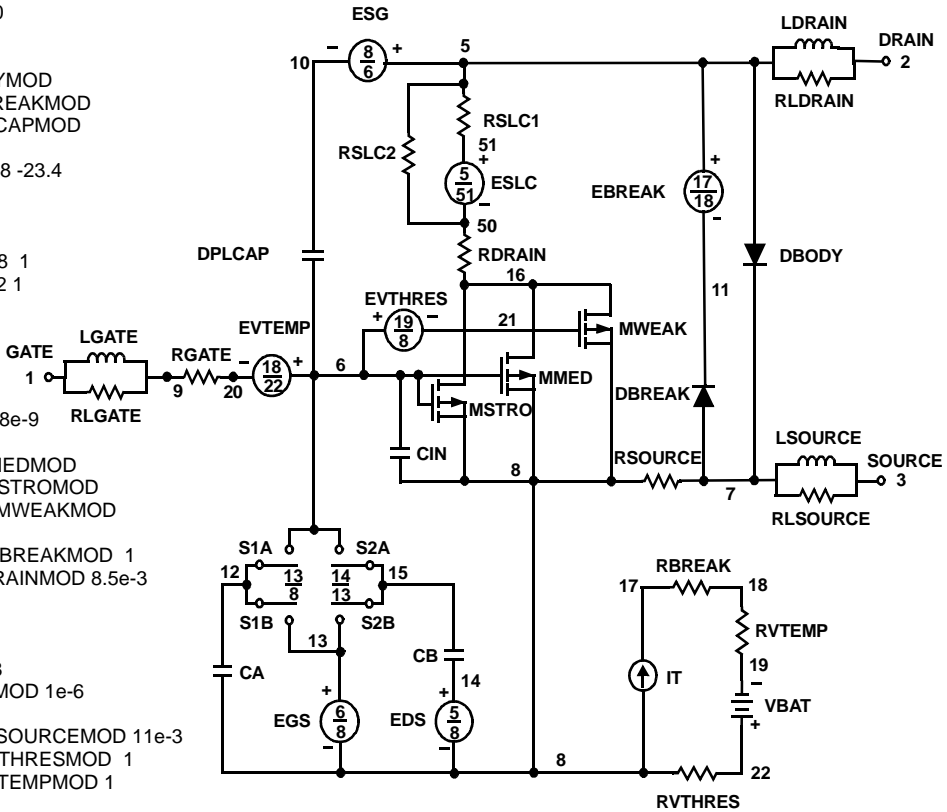
.MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 1.0 VOFF= 3.0)

.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0.5 VOFF= -0.3)

.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -0.3 VOFF= 0.5)

.ENDS

Note: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.



SPICE Thermal Model

REV October 2001
 FDM606P_JA Junction Ambient
 Copper Area= 1sq.in

CTHERM1 Junction c2 2e-4
 CTHERM2 c2 c3 3.0e-4
 CTHERM3 c3 c4 7.0e-4
 CTHERM4 c4 c5 2.0e-3
 CTHERM5 c5 c6 6.4e-3
 CTHERM6 c6 c7 3.0e-2
 CTHERM7 c7 c8 2.8e-1
 CTHERM8 c8 Ambient 2.9

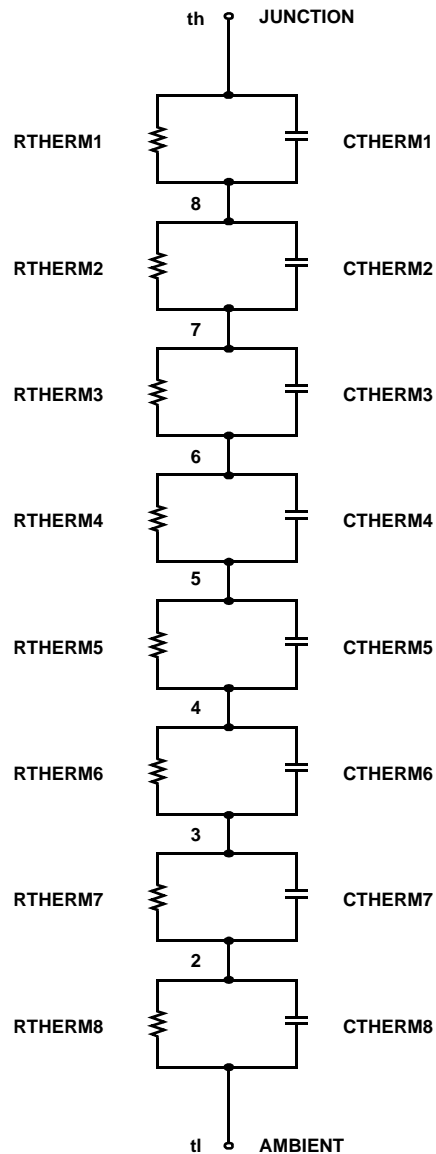
RTHERM1 Junction c2 1.0
 RTHERM2 c2 c3 1.3
 RTHERM3 c3 c4 2.5
 RTHERM4 c4 c5 3.0
 RTHERM5 c5 c6 4.0
 RTHERM6 c6 c7 7.7
 RTHERM7 c7 c8 12.7
 RTHERM8 c8 Ambient 24

SABER Thermal Model

SABER thermal model FDM606P
 Copper Area= 1sq.in
 template thermal_model th tl
 thermal_c th, tl

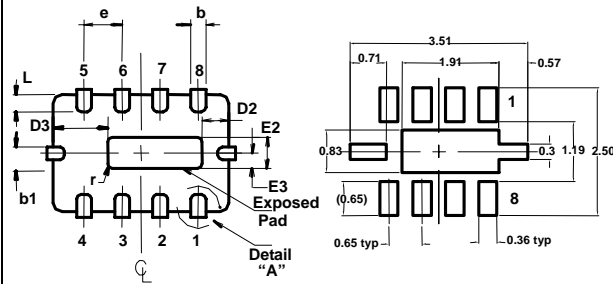
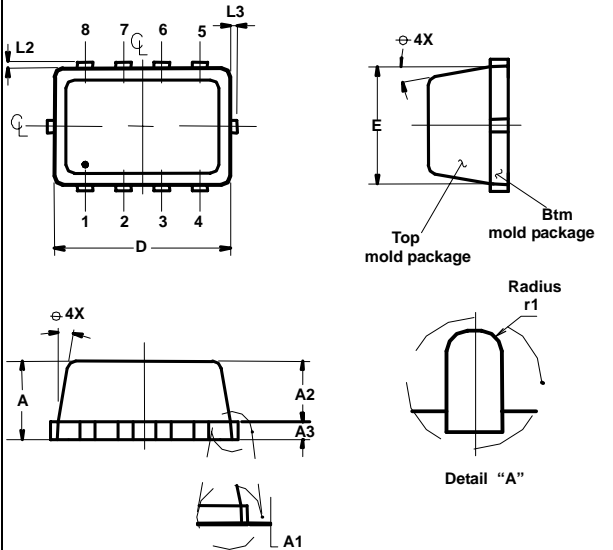
```
{
  ctherm.ctherm1 th c2 = 2.0e-4
  ctherm.ctherm2 c2 c3 = 3.0e-4
  ctherm.ctherm3 c3 c4 = 7.0e-4
  ctherm.ctherm4 c4 c5 = 2.0e-3
  ctherm.ctherm5 c5 c6 = 6.4e-3
  ctherm.ctherm6 c6 c7 = 3.0e-2
  ctherm.ctherm7 c7 c8 = 2.8e-1
  ctherm.ctherm8 c8 tl = 2.9
```

```
rtherm.rtherm1 th c2 = 1.0
rtherm.rtherm2 c2 c3 = 1.3
rtherm.rtherm3 c3 c4 = 2.5
rtherm.rtherm4 c4 c5 = 3.0
rtherm.rtherm5 c5 c6 = 4.0
rtherm.rtherm6 c6 c7 = 7.7
rtherm.rtherm7 c7 c8 = 12.7
rtherm.rtherm8 c8 tl = 24
}
```



MicroFET 3x2-8

SURFACE MOUNT JEDEC MicroFET 3x2-8 PLASTIC PACKAGE



Recommended land pattern

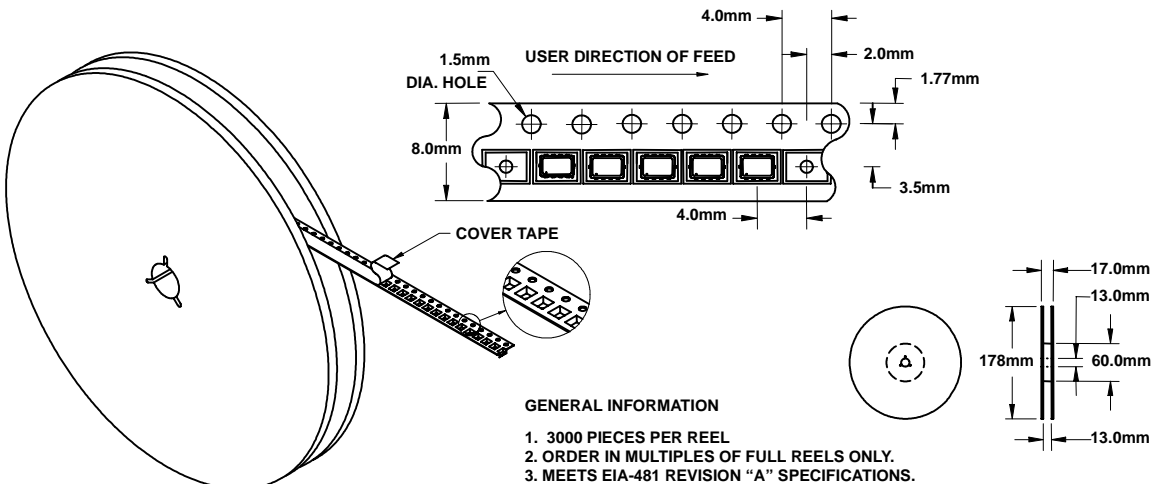
SYMBOL	MILLIMETERS		NOTES
	MIN	MAX	
A	0.80	1.00	1
A1	0.00	0.05	1
A2	0.65	0.75	1
A3	0.15	0.25	1
b	0.12	0.28	1
b1	0.24	0.50	1
D	2.90	3.10	1
E	1.90	2.10	1
D2	0.46	0.61	1
E2	0.45	0.60	1
D3	0.91	1.02	1
E3	0.15	0.35	1
e	0.65 BSC		1
L	0.21	0.37	1
L2	0.00	0.10	1
L3	0.00	0.10	1
N	8		4
r	0.127 BSC		1
r1	0.127 BSC		1
∅	0°	12°	

NOTES:

1. All dimensions are in mm.
2. Package outline exclusive of mold flash & metal burr.
3. Package outline inclusive of plating.
4. N is the total number of terminals.
5. Package surface finishing of Ra 0.4 um max.

MicroFET 3x2-8

8mm TAPE REEL



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Bottomless™	FPST™	MICROCOUPLER™	PowerSaver™	SuperSOT™-3
CoolFET™	FRFET™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	GlobalOptoisolator™	MicroPak™	QFET®	SuperSOT™-8
DOMET™	GTO™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	HiSeC™	MSX™	QT Optoelectronics™	TinyLogic®
E ² CMOS™	ꝑC™	MSXPro™	Quiet Series™	TINYOPTO™
EnSigna™	i-Lo™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
FACT Quiet Series™		OPTOLOGIC®	µSerDes™	UltraFET®
Across the board. Around the world.™		OPTOPLANAR™	SILENT SWITCHER®	UniFET™
The Power Franchise®		PACMAN™	SMART START™	VCX™
Programmable Active Droop™		POP™	SPM™	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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